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U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

INFORMATION DISCLOSURE STATEMENT BY APPLICANT (37 CFR 1.98(b))

Attorney Docket No.: P2001,0216	Applic. No. 10/673,705
Applicant	
Annalisa Ca	ippellani et al.
Filing Date	Group Art Unit
September 26, 2003	3

## **U.S. PATENT DOCUMENTS**

EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
506	Α	6,277,699 B1	08/21/01	Chen et al.			
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## FOREIGN PATENT DOCUMENT

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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Sheet 1 of 3

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506	C	5,384,479	1/24/95	Taniguchi	<b>-</b>		<del>                                     </del>		
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586	Mid-com D. Hall 18								
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536	K	02/41383 A1	5/23/02	WIPO			X	
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		Lasky, J. B. et al.:	Compariso	on of Transformation	to Low-Re	sistivity F	hase	
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